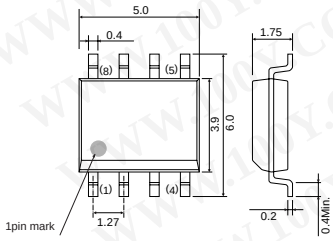
4V Drive Nch+Pch MOS FET

SP8M2

●Structure
Silicon N-channel MOS FET /
Silicon P-channel MOS FET

●External dimensions (Unit : mm)

SOP8



Each lead has same dimensions

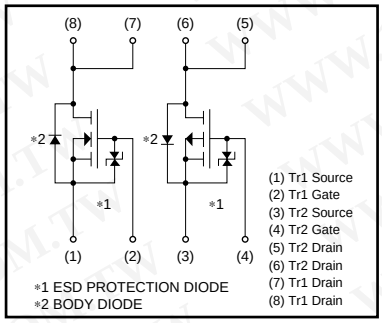
●Features
1) Low on-resistance.
2) Built-in G-S protection diode.
3) Small surface mount package (SOP8).

●Applications
Switching

●Package specifications

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
SP8M2		○

●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits		Unit
			Tr1 : N-ch	Tr2 : P-ch	
Drain-source voltage		V_{DSS}	30	−30	V
Gate-source voltage		V_{GSS}	20	−20	V
Drain current	Continuous	I_D	±3.5	±3.5	A
	Pulsed	I_{DP} *1	±14	±14	A
Source current (Body diode)	Continuous	I_S	1.6	−1.6	A
	Pulsed	I_{SP} *1	14	−14	A
Total power dissipation		P_D *2	2.0		W / TOTAL
Channel temperature		Tch	150		°C
Storage temperature		Tstg	−55 to +150		°C

*1 Pw≤10μs, Duty cycle≤1%
*2 Mounted on a ceramic board.

N-ch

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	10	μA	V_{GS}=20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	30	–	–	V	I_D= 1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	V_{DS}= 30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	1.0	–	2.5	V	V_{DS}= 10V, I_D= 1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	59	83	mΩ	I_D= 3.5A, V_{GS}= 10V
		–	93	130	mΩ	I_D= 3.5A, V_{GS}= 4.5V
		–	107	150	mΩ	I_D= 3.5A, V_{GS}= 4V
Forward transfer admittance	$\|Y_{fs}\|$ *	2.0	–	–	S	V_{DS}= 10V, I_D= 3.5A
Input capacitance	C_{iss}	–	140	–	pF	V_{DS}= 10V
Output capacitance	C_{oss}	–	45	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	30	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	6	–	ns	V_{DD}≒ 15V
Rise time	t_r *	–	6	–	ns	I_D= 1.75A
Turn-off delay time	$t_{d\ (off)}$ *	–	17	–	ns	V_{GS}= 10V R_L= 8.57Ω
Fall time	t_f *	–	4	–	ns	R_G=10Ω
Total gate charge	Q_g *	–	2.5	3.5	nC	V_{DD}≒15V, V_{GS}= 5V
Gate-source charge	Q_{gs} *	–	0.8	–	nC	I_D= 3.5A
Gate-drain charge	Q_{gd} *	–	0.8	–	nC	R_L= 4.29Ω, R_G= 10Ω

*Pulsed

●**Body diode characteristics** (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}*	–	–	1.2	V	I_S= 6.4A, V_{GS}=0V

*Pulsed

P-ch

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	–10	μA	V_{GS}= –20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	–30	–	–	V	I_D= –1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	V_{DS}= –30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	–1.0	–	–2.5	V	V_{DS}= –10V, I_D= –1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	65	90	mΩ	I_D= –3.5A, V_{GS}= –10V
		–	100	140	mΩ	I_D= –1.75A, V_{GS}= –4.5V
		–	120	165	mΩ	I_D= –1.75A, V_{GS}= –4V
Forward transfer admittance	$\|Y_{fs}\|$ *	1.8	–	–	S	V_{DS}= –10V, I_D= –1.75A
Input capacitance	C_{iss}	–	490	–	pF	V_{DS}= –10V
Output capacitance	C_{oss}	–	110	–	pF	V_{GS}= 0V
Reverse transfer capacitance	C_{rss}	–	75	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	10	–	ns	V_{DD}≒ –15V
Rise time	t_r *	–	15	–	ns	I_D= –1.75A
Turn-off delay time	$t_{d\ (off)}$ *	–	35	–	ns	V_{GS}= –10V
Fall time	t_f *	–	10	–	ns	R_L= 8.57Ω R_G= 10Ω
Total gate charge	Q_g *	–	5.5	7.7	nC	V_{DD}≒ –15V, V_{GS}= –5V
Gate-source charge	Q_{gs} *	–	1.5	–	nC	I_D= –3.5A
Gate-drain charge	Q_{gd} *	–	2.0	–	nC	R_L= 4.29Ω, R_G= 10Ω

*Pulsed

●**Body diode characteristics** (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}*	–	–	–1.2	V	I_S= –1.6A, V_{GS}=0V

*Pulsed

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